Ordering number : ENA0073

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

ECH8411 — General-Purpose Switching Device Applications

Features

- Ultrahigh-speed switching.
- 1.8V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		9	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	36	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	0.5		1.3	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=4A	7	12		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=4A, V_{GS}=4V		12	16	mΩ
	$R_{DS}(on)2$	I_D=2A, V_{GS}=2.5V		16	23	mΩ
	$R_{DS}(on)3$	I_D=2A, V_{GS}=1.8V		25	36	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		1740		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		310		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		290		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		30		ns
Rise Time	t_r	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		240		ns
Fall Time	t_f	See specified Test Circuit.		210		ns

Marking : KR

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SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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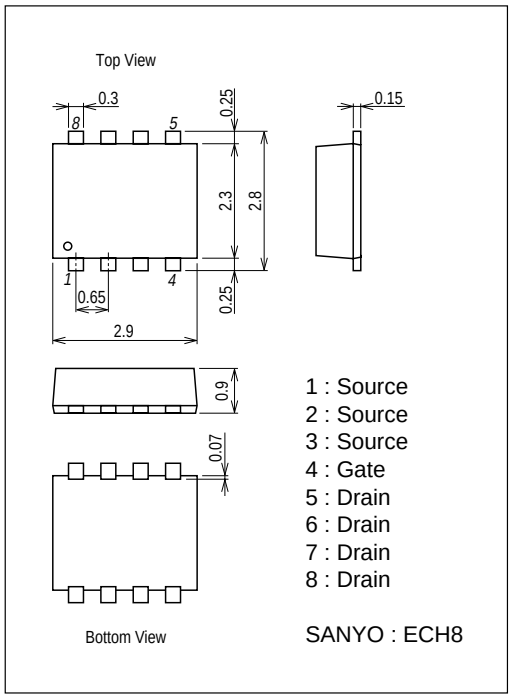
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4V, I_D=9A		21		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=4V, I_D=9A		3.5		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=4V, I_D=9A		6.2		nC
Diode Forward Voltage	V_{SD}	I_S=9A, V_{GS}=0V		0.84	1.2	V

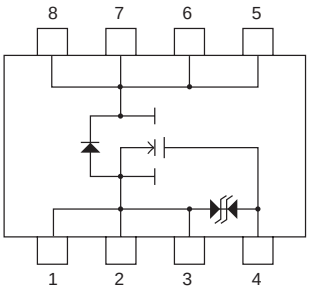
Package Dimensions

unit : mm

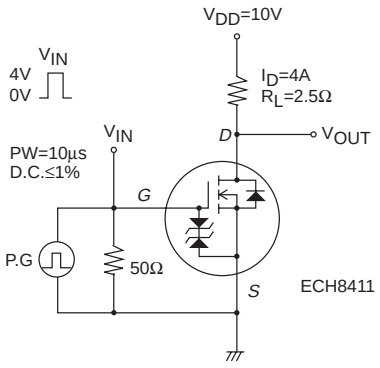
7011-002

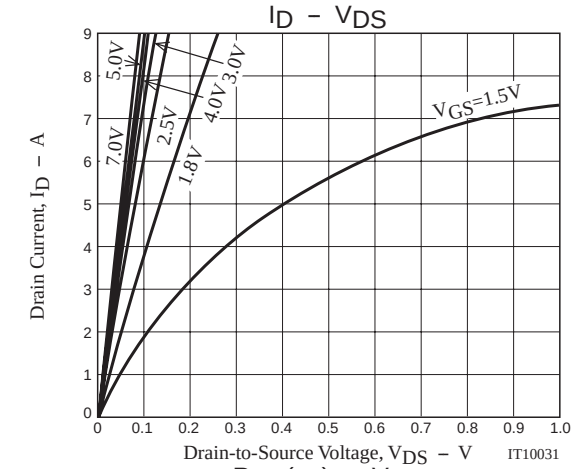


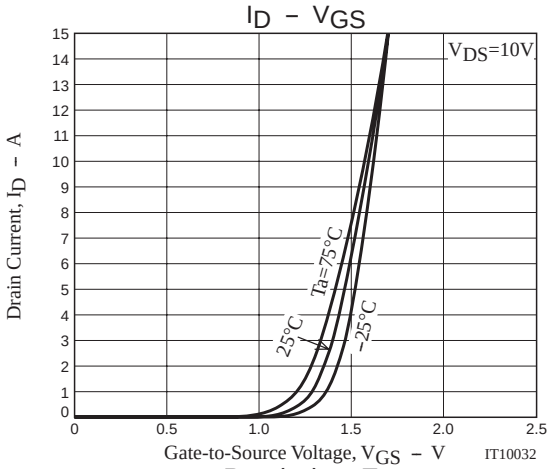
Electrical Connection

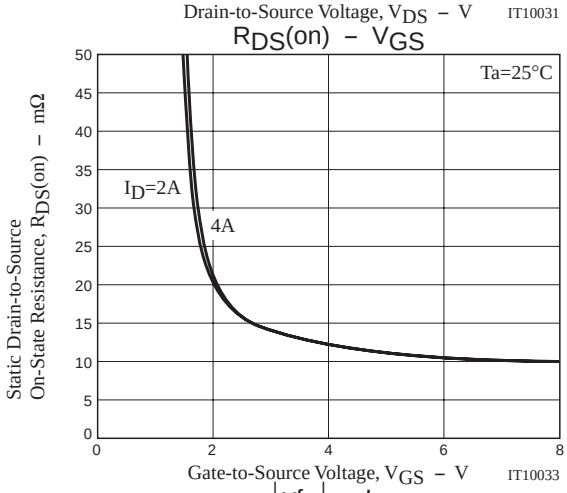


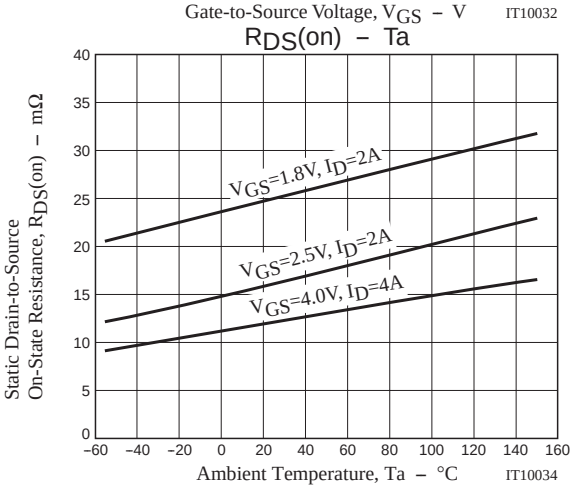
Switching Time Test Circuit

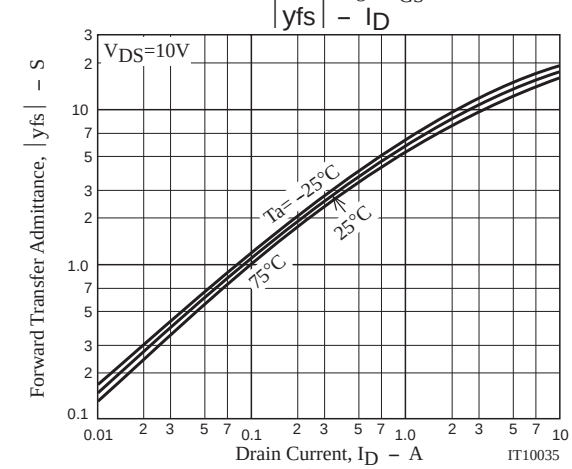


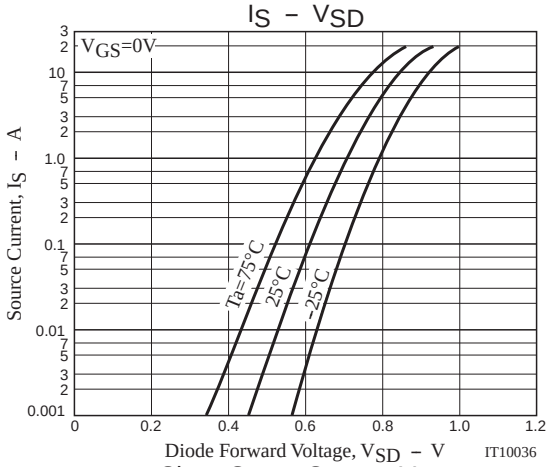


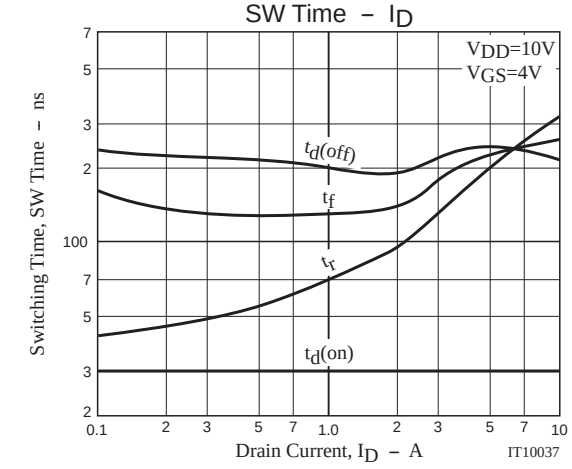


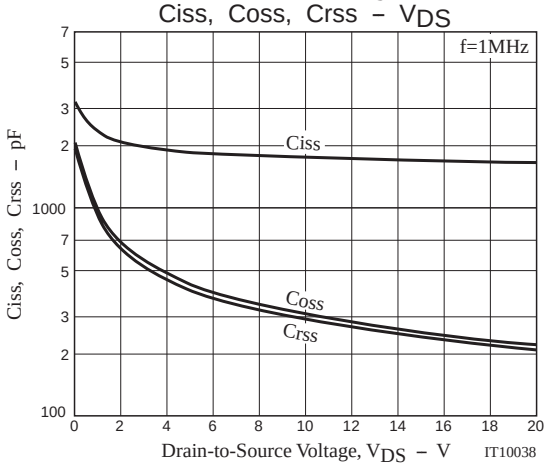


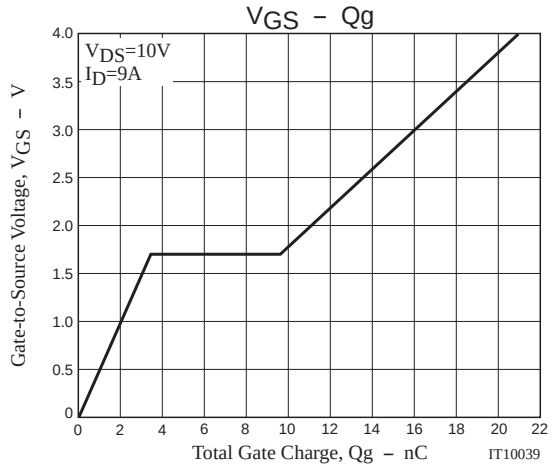


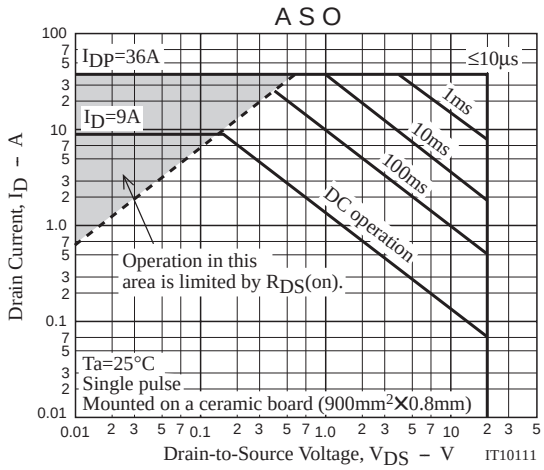


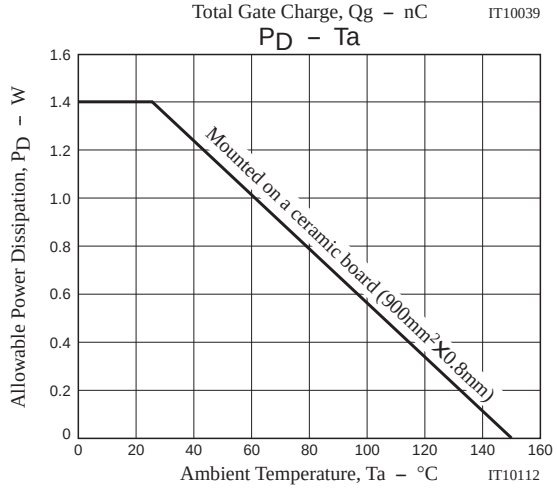












Note on usage : Since the ECH8411 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.